

## P-Channel Enhancement Mode MOSFET

### Feature

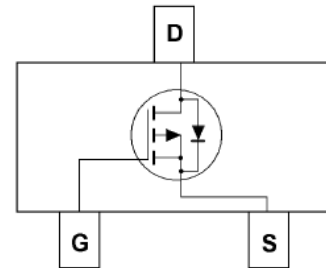
- -30V/-3.8A,  $R_{DS(ON)}=55m\Omega(MAX)$  @  $V_{GS} = -10V$ .  
 $R_{DS(ON)} = 70m\Omega(MAX)$  @  $V_{GS} = -4.5V$ .  
 $R_{DS(ON)} = 120m\Omega(MAX)$  @  $V_{GS} = -2.5V$ .
- Super High dense cell design for extremely low  $R_{DS(ON)}$
- Reliable and Rugged
- SOT-23 for Surface Mount Package



SOT-23

### Applications

- Power Management
- Portable Equipment and Battery Powered Systems.



### Absolute Maximum Ratings $T_A=25^\circ C$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	-3.8	A

### Electrical Characteristics $T_A=25^\circ C$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24V, V_{GS}=0V$	-	-	-1	$\mu A$
Gate Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS}=12V, V_{DS}=0V$	-	-	100	nA
Gate Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS}=-12V, V_{DS}=0V$	-	-	-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.7	-	-1.3	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -4.2A$	-	50	55	$m\Omega$
		$V_{GS} = -4.5V, I_D = -4.0A$	-	60	70	$m\Omega$
		$V_{GS} = -2.5V, I_D = -1.0A$	-	80	120	$m\Omega$
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	VSD	$V_{GS} = 0V, I_S = -1.0A$			-1.0	V

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## Typical Characteristics

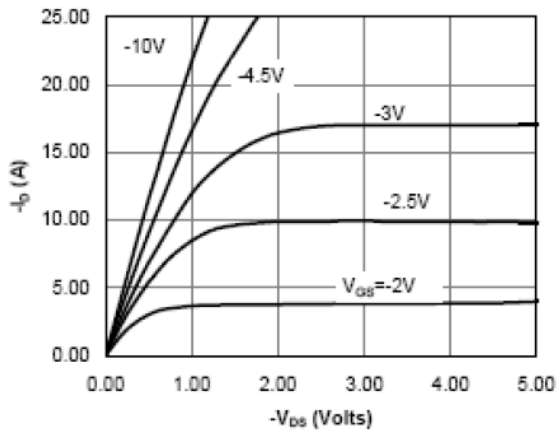


Fig 1: On-Region Characteristics

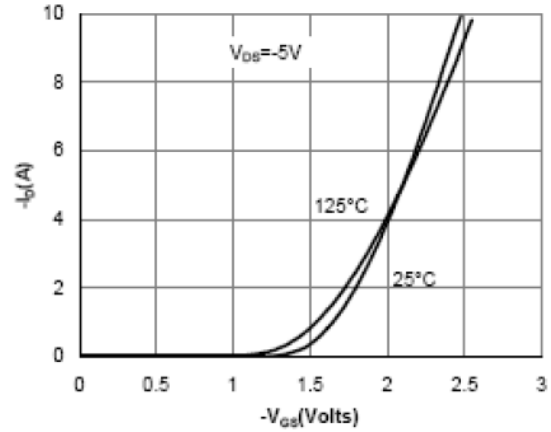


Figure 2: Transfer Characteristics

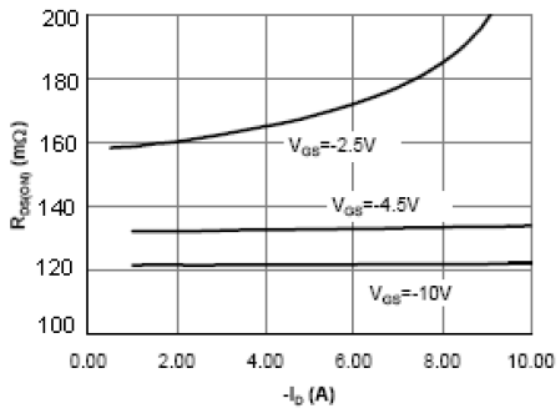


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

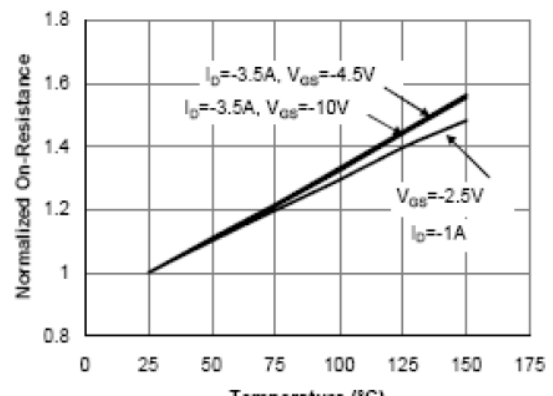


Figure 4: On-Resistance vs. Junction Temperature

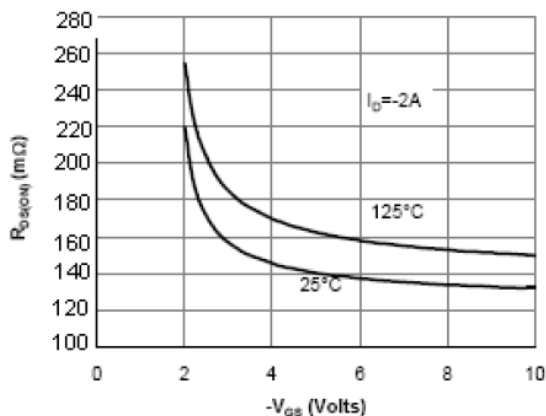


Figure 5: On-Resistance vs. Gate-Source Voltage

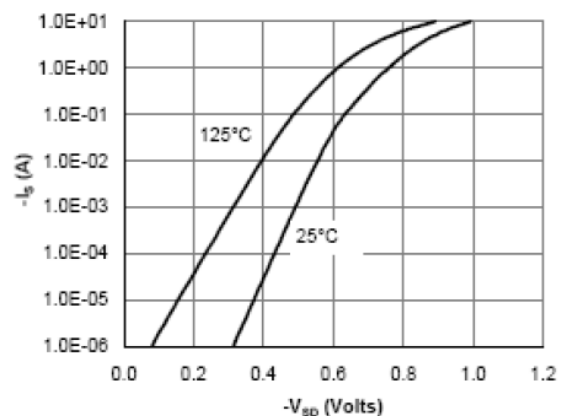


Figure 6: Body-Diode Characteristics

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